

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

### LISTING OF CLAIMS

1. (currently amended) A purifier for use in a gas processing application, ~~the purifier~~ comprising:
  - a chamber having a gas inlet and a gas outlet;
  - at least one series of baffles arranged in the chamber and ~~coated with~~ having a coating comprising a getter material selected for its ability to react with species to be removed from a gas stream and form stable compounds,
  - a source of the getter material ~~provided within the chamber;~~ and
  - means for activating the source of the getter material to refresh the coating of getter material on the at least one baffles.
2. (currently amended) ~~The A~~-purifier according to Claim 1; wherein the means for activating the source of the getter material ~~comprises means for vaporising~~ vaporizes the source of the getter material.
3. (currently amended) ~~The A~~ purifier according to Claim 2; further comprising a collector wherein the ~~vaporising~~ means for activating the source of the getter material is arranged to produce an electric arc between the source of the getter material and a ~~the~~ collector.
4. (currently amended) ~~The A~~ purifier according to Claim 3; wherein the collector extends about the source of the getter material.
5. (currently amended) ~~The A~~ purifier according to Claim 3 further comprising an inner wall of the chamber ~~or Claim 4~~; wherein the collector comprises at least part of the inner wall of the chamber.

6. (currently amended) TheA purifier according to ~~any preceding~~ Claim 1, wherein the source of the getter material comprises a rod ~~of getter material~~, the at least one baffles being arranged about ~~and along~~ the rod.
7. (currently amended) TheA purifier according to Claim 6; wherein the rod extends longitudinally through the chamber.
8. (currently amended) TheA purifier according to Claim 7; wherein the rod is substantially co-axial with the chamber.
9. (currently amended) TheA purifier according to ~~any preceding~~ Claim 1, ~~comprising wherein the means for activating the source of the getter material comprises a controller.~~ ~~controlling the activation of the activation means.~~
10. (currently amended) TheA purifier according to Claim 9; wherein the controller ~~means is configured~~ adapted to activate ~~the activation means~~ at predefined time intervals.
11. (currently amended) TheA purifier according to Claim 10; ~~wherein the control means comprises at least one~~ further comprising a sensor for monitoring a process gas ~~an environment within or outside of the chamber and for activating the activation means wherein the source of the getter material is activated when a predefined change in the monitored environment~~ process gas is detected by the sensor.
12. (currently amended) TheA purifier according to Claim 11; wherein ~~said at least one~~ the sensor is located within the chamber.
13. (currently amended) TheA purifier according to ~~any preceding~~ Claim 1, wherein the at least one baffles is ~~are configured and/or arranged so as~~ adapted to create a convoluted path for gas flowing through the chamber.
14. (currently amended) TheA purifier according to ~~any preceding~~ Claim 1, wherein the getter material ~~is~~ comprises at least one metal selected from the group of metals consisting of; Ti, Ta, ~~and~~ Zr, and alloys thereof.

15. (currently amended) ~~The~~A purifier according to ~~any of~~ Claims 1 to 13, wherein the getter material ~~is comprises~~ at least one metal selected from; the group of metals consisting of Fe, and Cr, and alloys thereof.

16. (currently amended) A semiconductor processing system comprising:  
a process chamber ~~for receiving a process gas~~having a purified gas inlet; and  
a purifier comprising:

a housing;

a gas inlet;

a gas outlet upstream of the purified gas inlet;

at least one baffle arranged within the housing and comprising a getter material;

a source of the getter material; and

a means for applying an electric potential across the source of the getter material and the housing.

~~according to any preceding claim for purifying the process gas upstream from the process chamber.~~

17. (new) The semiconductor processing system of claim 16 wherein the source of the getter material is a rod.

18. (new) The semiconductor processing system of claim 16 wherein the source of the getter material is an electrode.

19. (new) The semiconductor processing system of claim 16 wherein the at least one baffle is arranged to form a convoluted flow path.

20. (new) The semiconductor processing system of claim 19 wherein the at least one baffle is arranged about the source of the getter material.

21. (new) The semiconductor processing system of claim 16 wherein the means for applying an electric potential comprises a power supply.

22. (new) The semiconductor processing system of claim 16 wherein the means for applying an electric potential comprises a controller for activating the source of the getter material at predefined time intervals.

23. (new) The semiconductor processing system of claim 16 wherein the getter material comprises at least one metal selected from the group of metals consisting of Ti, Ta, Zr, Fe, Cr and alloys thereof.